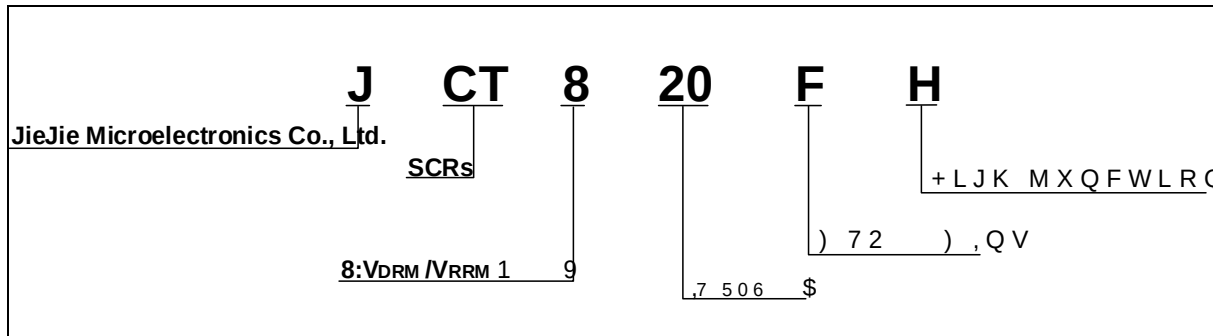


gate power dissipation P_{T150}	$3^* \$9$		
JDWH SRZHU	3^*0		:
SXOVH YROWDJH QRQ UHSHWLWLYH RII V_{SS} VWDWH), *			

Test Condition	Value			Unit
	MIN.	TYP.	MAX.	

$V_D = V_{RM}$ $T_f = 150$	-	-	1	V
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h w5 9 wLbD LbC h wa ! ¢ L h b



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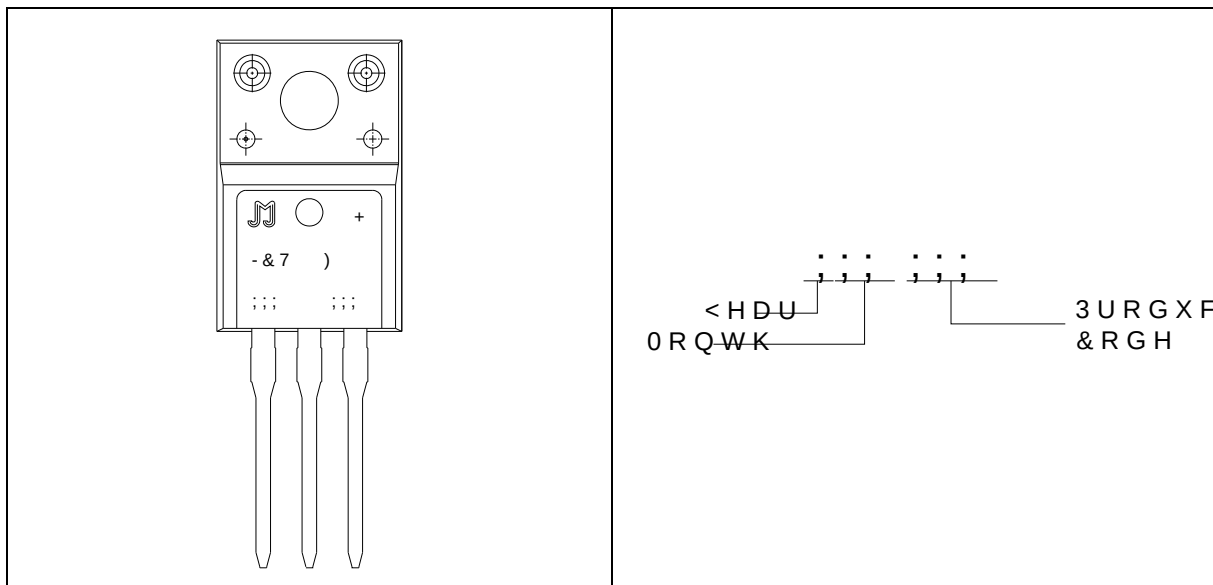
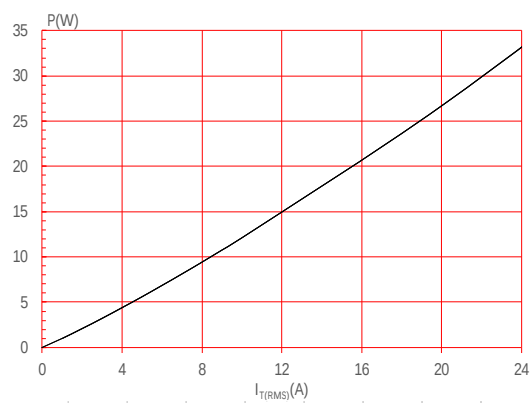
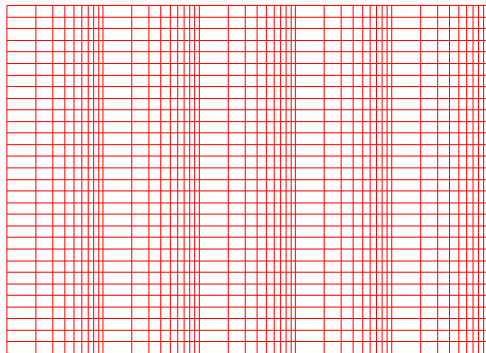
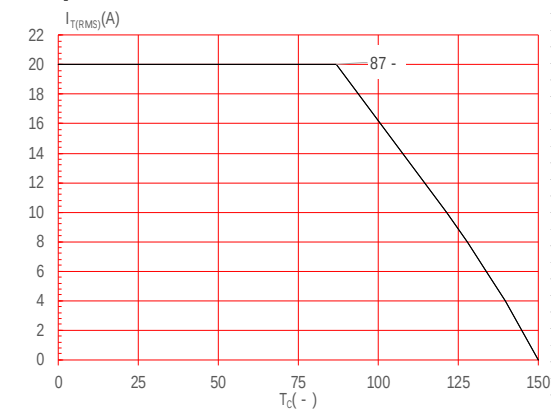
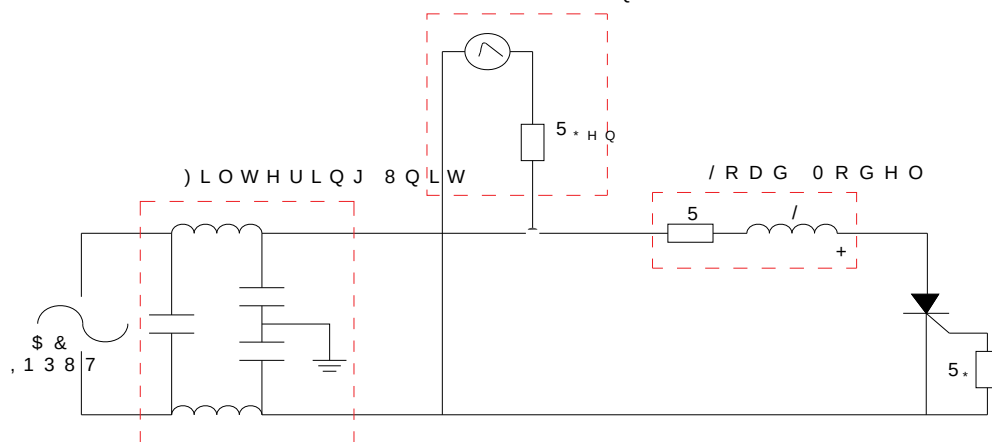


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.3: Surge peak on-state current versus number of cycles

FIG.2: RMS on-state current versus case temperature

FIG.4: On-state characteristics

```

, ( &                6 W D Q G D U G V
  6 X U J H * H Q H U D W R U
    6 Y R O W D J H V X U J H
      6 F X U U H Q W V X U J H

```





h w5 9 wLbD LbC h wa ! ¢ L h b

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT820FH	800	15	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	C h a n g e s
Jun.15, 2023	A.1.0	Last update
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

JCT820FH

 JieJie Microelectronics Co., Ltd.

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